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- 19. (New) Detector according to Claim 15, wherein said insulating fabric is a woven fabric.
- 20. (New) Detector according to Claim 15, wherein said insulating fabric is a non-woven fabric.
- 21. (New) Detector according to Claim 15, wherein said electrode structures are deposited on said insulating fabric.
- 22. (New) Detector according to Claim 15, comprising a metallic layer, which is deposited on said insulating fabric, wherein said electrode structures are engraved or etched in said metallic layer.
- 23. (New) Detector according to Claim 15, wherein said layer of semiconducting material comprises a conducting elastomer, granulated or non-granulated, which is deposited or stuck on said electrode structures.
- 24. (New) Detector according to Claim 15, wherein the layer of semiconducting material is divided into several zones, said zones being arranged at different places on said electrode structures, thus defining several active zones of said detector.
- 25. (New) Detector according to Claim 15, further comprising a protective layer applied onto said electrode structures and said layer of semiconducting material.
- 26. (New) Vehicle seat comprising at least one passenger detector according to Claim
 15.
- 27. (New) Vehicle seat according to Claim 26, wherein said passenger detector is integrated into the surface of the seat.

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- 28. (New) Vehicle seat according to Claim 26, wherein said passenger detector is integrated into the into the back of the seat.
- 29. (New) Vehicle seat according to Claim 26, wherein said passenger detector is integrated the head-rest.

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(New) Passenger detector having a plurality of active zones, said detector comprising a flexible support made of an insulating fabric, at least two electrode structures arranged on said insulating fabric at a distance from each other, and a layer of semiconducting material, said layer of semiconducting material having an internal resistance that varies with a deformation of said layer, said layer of semiconducting material being divided into several zones, each of said zones being arranged in one of said active zones of said detector on said electrode structures and in intimate contact with said electrode structures.